

INCHANGE SEMICONDUCTOR

isc N-Channel MOSFET Transistor

SPA11N80C3

• FEATURES

- New revolutionary high voltage technology
- Ultra low gate charge
- · High peak current capability
- Improved transconductance
- 100% avalanche tested
- · Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

· Switching applications

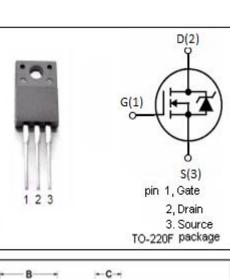
• ABSOLUTE MAXIMUM RATINGS(Ta=25℃)							
SYMBOL	PARAMETER	VALUE	UNIT				
V _{DSS}	Drain-Source Voltage	800	V				
V _{GSS}	Gate-Source Voltage	±20	V				
ID	Drain Current-Continuous@Tc=25℃ Tc=100℃	11 7.1	А				
I _{DM}	Drain Current-Single Pulsed	33	A				
PD	Total Dissipation	41	W				
Tj	Operating Junction Temperature	-55~150	°C				
T _{stg}	Storage Temperature	-55~150	°C				

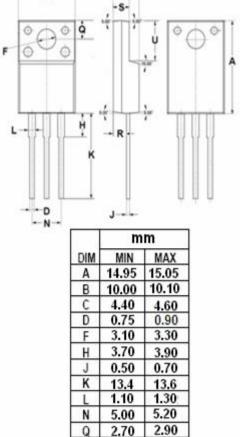
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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER		UNIT	
Rth(ch-c)	Channel-to-case thermal resistance	3.7	°C/W	
Rth(ch-a)	Channel-to-ambient thermal resistance	62	°C /W	

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2.40

2.90

6.60

isc website: www.iscsemi.cn

R

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2.20 2.65

6.40



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ELECTRICAL CHARACTERISTICS

$T_{C}\text{=}25^{\circ}\!\!\!\mathrm{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D = 0.25mA	800			V
V _{GS} (th)	Gate Threshold Voltage	V _{DS} =±20V; I _D =0.68mA	2.1		3.9	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = 10V; I _D =7.1A		390	450	mΩ
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ±20V;V _{DS} = 0V			±0.1	μA
I _{DSS}	Drain-Source Leakage Current	V _{DS} = 800V; V _{GS} = 0V; T _J =25°C T _J =125°C			20 200	μA
V _{SDF}	Diode forward voltage	I _{SD} =11A, V _{GS} = 0 V			1.2	v

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2